

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	410337	(lcd or liquid adj crystal adj display)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:17
L5	31962	interconnect\$3 adj (line\$1 or wir\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:20
L6	1317	(Interconnect\$3 adj (line\$1 or wir\$4)) near5 (width)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:18
L7	2	4 with 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:18
L8	218	((narrow or wide\$2 or small\$2 or larger\$2 or great\$2) adj width) same 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:20
L9	4054	(interconnect\$3 near5 (line\$1 or wir\$4)) with resistance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:21
L10	53	8 and 9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:21
L11	2	4 and 10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:21

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L12	10	4 and 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:22
L13	22116	(center adj (part or portion)) with (great\$2 or larg\$2 or wid\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:23
L14	6	5 same 13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:25
L15	968	(wir\$3 or line\$1) with (center adj (part or portion)) with (great\$2 or larg\$2)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:26
L16	158	4 with 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:26
L17	1	15 and 16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:26
L18	1	6 and 15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:27
L19	5	4 with 15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:27

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L3	0	((lcd or liquid adj crystal adj display) with (data adj interconnection adj line\$1) with (driving adj circuit) and (pluality adj gate adj line\$1) same (plurality adj data adj line\$1) same (tft or thin adj film adj transistor\$1) and (forming adj first adj active layer) with (island adj shape) with (tft or thin adj film adj transistor\$1) with (second adj active layer) with (substrate\$1) and (forming adj gate adj insulating adj film) with (entire adj surface) with (first adj active adj layer) with (second adj layer adj active) and (forming adj source adj region) with (drain adj region) with (first adj active adj layer) with (impurity adj ion adj implantation) with (gate adj electrode\$1) with mask and (forming adj conductive adj layer) with (second adj active adj layer) and (forming adj interlayer adj insulating film) with (entire adj surface) with (source adj region) with (drain adj reion) with (form\$3 adj contact adj hole) and (first adj width) with (data adj interconnection adj line\$1) with (center adj portion) with (data adj interconnection adj line\$1) with (great\$2 or larger) with (second adj width adj data adj interconnection adj line\$1) with (outer adj portion) with (data adj interconnection adj line\$1) and (capacitance adj data adj interconecion adj line\$1) with (second adj active adj layer) with (gradually adj increas\$3) with (center adj portion) with (outer adj portion)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/04/28 11:11